

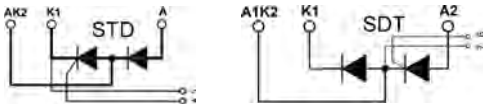
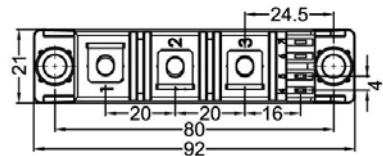
STD70GKxxB

Thyristor-Diode Modules



Type	V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V
STD70GK08B	900	800
STD70GK12B	1300	1200
STD70GK14B	1500	1400
STD70GK16B	1700	1600
STD70GK18B	1900	1800

Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions		Maximum Ratings	Unit
I_{TRMS} , I_{FRMS} I_{TAVM} , I_{FAVM}	$T_{VJ}=T_{VJM}$ $T_C=85^{\circ}C$; 180° sine		110 70	A
I_{TSM} , I_{FSM}	$T_{VJ}=45^{\circ}C$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	1600 1700	A
	$T_{VJ}=T_{VJM}$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	1450 1540	
$\int i^2 dt$	$T_{VJ}=45^{\circ}C$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	13200 13990	A ² s
	$T_{VJ}=T_{VJM}$ $V_R=0$	$t=10ms$ (50Hz), sine $t=8.3ms$ (60Hz), sine	9900 10500	
$(di/dt)_{cr}$	$T_{VJ}=T_{VJM}$ $f=50Hz$, $t_p=200\mu s$ $V_D=2/3V_{DRM}$ $I_G=0.45A$ $di_G/dt=0.45A/\mu s$	repetitive, $I_T=150A$	150	A/ μs
		non repetitive, $I_T=I_{TAVM}$	500	
$(dv/dt)_{cr}$	$T_{VJ}=T_{VJM}$; $R_{GK}=\infty$; method 1 (linear voltage rise)	$V_{DR}=2/3V_{DRM}$	1000	V/ μs
P_{GM}	$T_{VJ}=T_{VJM}$ $I_T=I_{TAVM}$	$t_p=30\mu s$ $t_p=300\mu s$	10 5	W
P_{GAV}			0.5	W
V_{RGM}			10	V
T_{VJ} T_{VJM} T_{stg}			-40...+125 125 -40...+125	$^{\circ}C$
V_{ISOL}	50/60Hz, RMS $I_{ISOL}\leq 1mA$	$t=1min$ $t=1s$	3000 3600	V~
M_d	Mounting torque (M5) Terminal connection torque (M5)		2.5-4.0/22-35 2.5-4.0/22-35	Nm/lb.in.
Weight	Typical including screws		120	g

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Symbol	Test Conditions	Characteristic Values	Unit
I_{RRM}, I_{DRM}	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	5	mA
V_T, V_F	$I_T, I_F=210A; T_{VJ}=25^{\circ}C$	1.60	V
V_{TO}	For power-loss calculations only ($T_{VJ}=125^{\circ}C$)	0.85	V
r_T		3.7	m Ω
V_{GT}	$V_D=6V;$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	1.5 1.6	V
I_{GT}	$V_D=6V;$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	100 200	mA
V_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.2	V
I_{GD}		10	mA
I_L	$T_{VJ}=25^{\circ}C; t_p=10\mu s; V_D=6V$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	450	mA
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	200	mA
t_{gd}	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	2	μs
t_q	$T_{VJ}=T_{VJM}; I_T=150A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=20V/\mu s; V_D=2/3V_{DRM}$ typ.	150	μs
Q_s	$T_{VJ}=T_{VJM}; I_T, I_F=50A; -di/dt=3A/\mu s$	100	μC
I_{RM}		24	A
R_{thJC}	per thyristor/diode; DC current per module	0.45 0.225	K/W
R_{thJK}	per thyristor/diode; DC current per module	0.65 0.325	K/W
d_s	Creeping distance on surface	12.7	mm
d_A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * Isolation voltage 3600 V~
- * UL file NO.310749
- * RoHS compliant

APPLICATIONS

- * DC motor control
- * Softstart AC motor controller
- * Light, heat and temperature control

ADVANTAGES

- * Space and weight savings
- * Simple mounting with two screws
- * Improved temperature and power cycling
- * Reduced protection circuits



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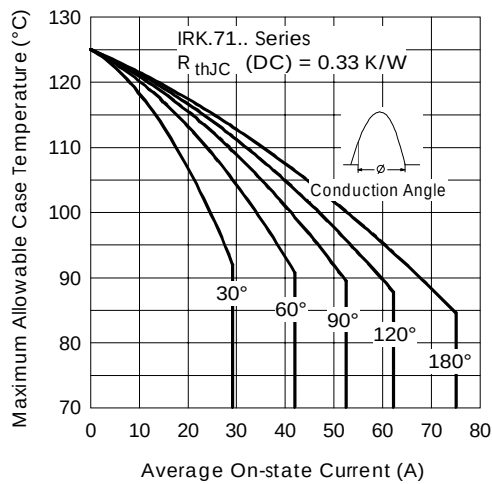


Fig. 1 - Current Ratings Characteristics

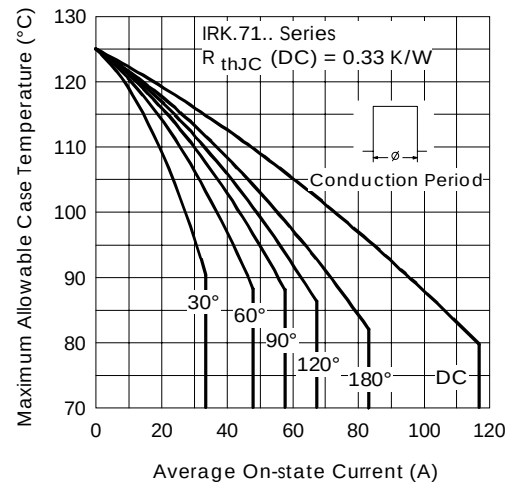


Fig. 2 - Current Ratings Characteristics

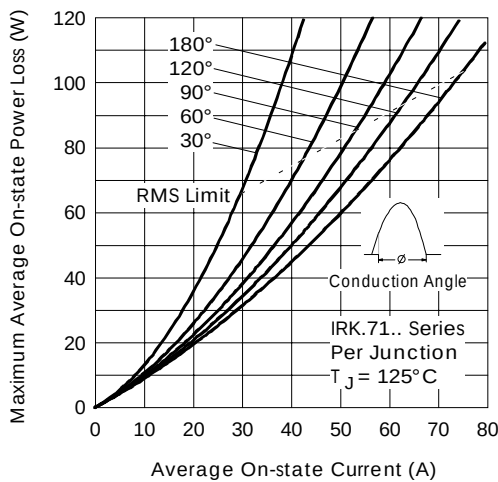


Fig. 3 - On-state Power Loss Characteristics

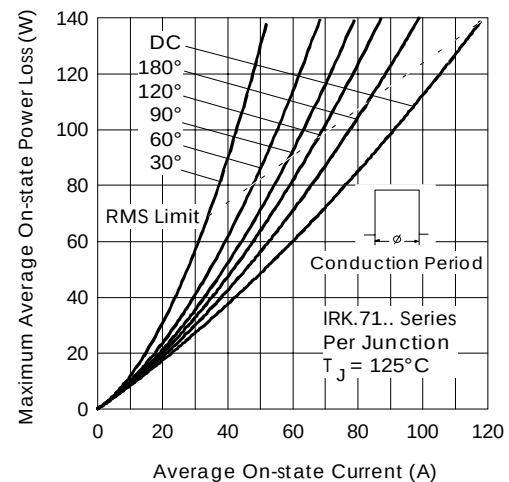


Fig. 4 - On-state Power Loss Characteristics

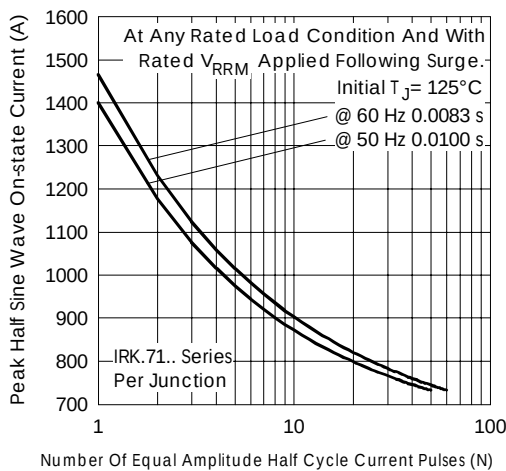


Fig. 5 - Maximum Non-Repetitive Surge Current

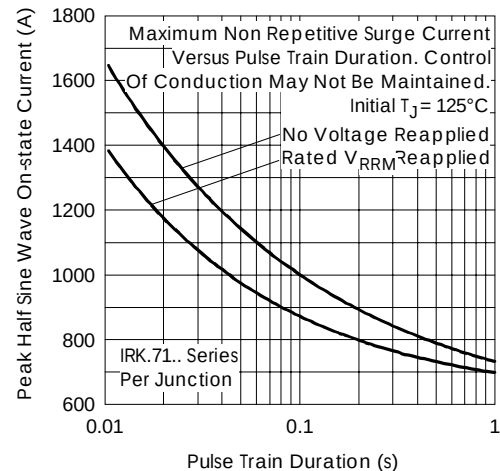


Fig. 6 - Maximum Non-Repetitive Surge Current

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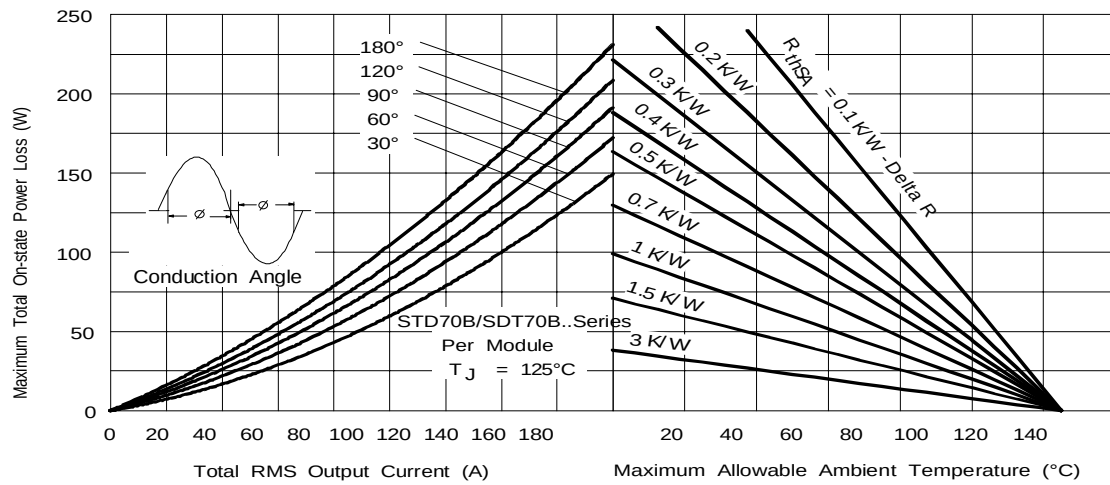


Fig. 7 - On-state Power Loss Characteristics

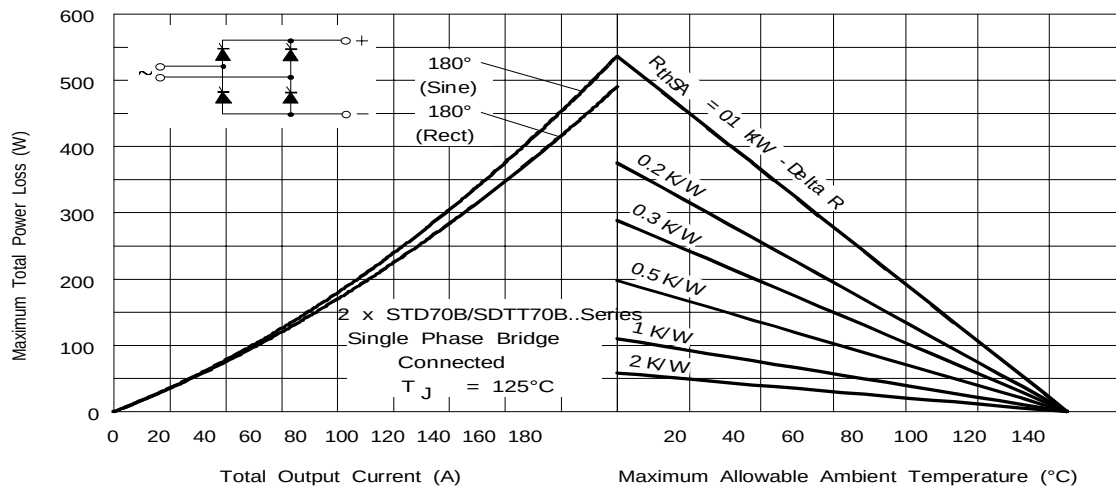


Fig. 8 - On-state Power Loss Characteristics

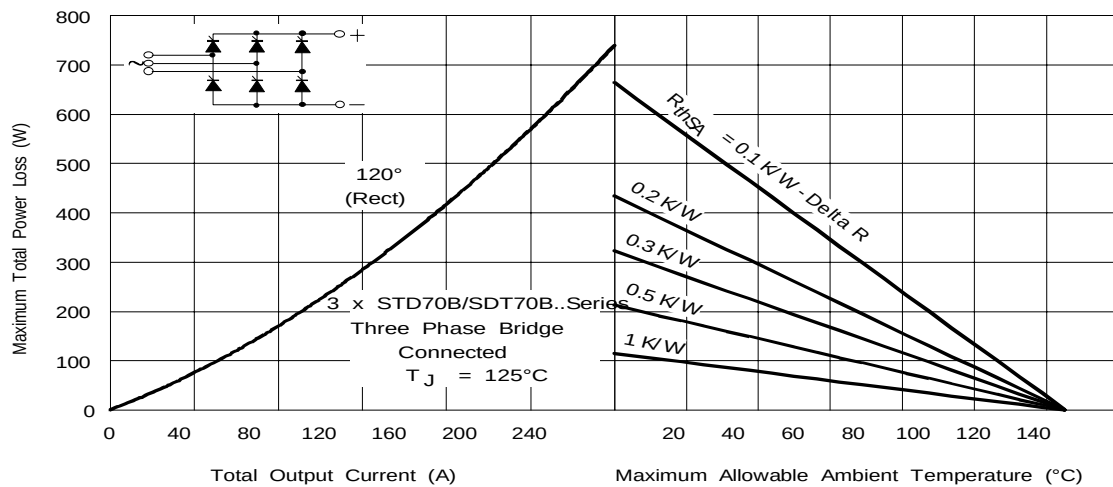


Fig. 9 - On-state Power Loss Characteristics

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